PZTA64 TRANSISTOR (PNP)

1.BASE
2.COLLECTOR
3.EMITTER

SOT-223

FEATURES

- Low Voltage and High Current
- High Current Gain Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CES}$	I_C=-0.1mA,I_B=0	-30			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V,I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-10V, I_C=0			-100	nA
DC current gain	$h_{FE(1)}$*	V_{CE}=-5V, I_C=-10mA	10000			
	$h_{FE(2)}$*	V_{CE}=-5V, I_C=-100mA	20000			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=-100mA,I_B=-0.1mA			-1.5	V
Base-emitter voltage	V_{BE}*	V_{CE}=-5V, I_C=-100mA			-2	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-10mA, f=100MHz	125			MHz

*Pulse test: pulse width ≤350μs, duty cycle≤ 2.0%.